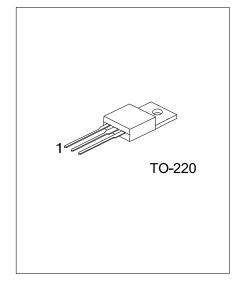
UTT80P06 Preliminary Power MOSFET

80A, 60V P-CHANNEL POWER MOSFET

■ DESCRIPTION

The UTC **UTT80P06** is a P-channel power MOSFET using UTC's advanced technology to provide the customers with high switching speed and a minimum on-state resistance, and it can also withstand high energy in the avalanche.

The UTC **UTT80P06** is suitable for low voltage and high speed switching applications



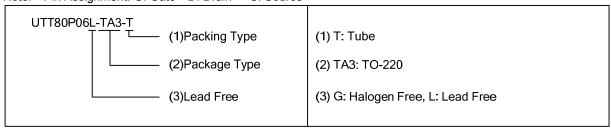
■ FEATURES

- * $R_{DS(ON)}$ =0.021 Ω @ V_{GS} =-10V, I_D =-64A
- * High Switching Speed

■ ORDERING INFORMATION

Ordering Number		Dookses	Pin Assignment			Doolsing
Lead Free	Halogen Free	Package	1	2	3	Packing
UTT80P06L-TA3-T	UTT80P06G-TA3-T	TO-220	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source



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■ **ABSOLUTE MAXIMUM RATINGS** (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V_{DSS}	-60	V	
Gate-Source Voltage		V_{GSS}	±20	V	
Drain Current	Continuous	T _C =25°C	- I _D	-80	Α
	Continuous	T _C =100°C		-64	Α
	Pulsed	T _C =25°C	I _{DM}	-320	Α
Avalanche Energy Single Pulsed Repetitive		Single Pulsed	E _{AS}	823	mJ
		Repetitive	E _{AR}	34	mJ
Power Dissipation T _C =25°C		T _C =25°C	P_{D}	313	W
Junction Temperature		T_J	+150	°C	
Storage Temperature		T _{STG}	-55~+150	°C	

Notes: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Case	θ_{JC}	0.4	°C/W
Junction to Ambient	θ_{JA}	62	°C/W

■ **ELECTRICAL CHARACTERISTICS** (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D =-250 μ A, V_{GS} =0V	-60			>
Drain-Source Leakage Current		I _{DSS}	V _{DS} =-60V, V _{GS} =0V, T _J =25°C		-0.1	-1	μΑ
			V _{DS} =-60V, T _C =150°C		-10	-100	μΑ
Gate-Source Leakage Current	Forward	I _{GSS}	V_{GS} =+20V, V_{DS} =0V			+100	nΑ
	Reverse		V_{GS} =-20V, V_{DS} =0V			-100	nΑ
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_{D}=-5.5$ mA	-2.1	-3	-4	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	I _D =-64A, V _{GS} =-10V		0.021	0.023	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}			4026	5033	pF
Output Capacitance		C_{OSS}	V _{GS} =0V, V _{DS} =-25V, f=1.0MHz		1252	1565	pF
Reverse Transfer Capacitance		C_{RSS}			437	546	pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{DD} =-48V, I_{D} =-80A, V_{GS} = -10V		115	173	nC
Gate to Source Charge		Q_GS	V _{DD} =-48V, I _D =-80A		27.4	41	nC
Gate to Drain Charge		Q_GD			50	75	nC
Turn-ON Delay Time		$t_{D(ON)}$			24	36	ns
Rise Time		t_R	V_{DD} =-30V, I_{D} =-64A, R_{G} =1 Ω ,		18	27	ns
Turn-OFF Delay Time		$t_{D(OFF)}$	V _{GS} =-10V		56	84	ns
Fall-Time		t_{F}			30	45	ns
SOURCE- DRAIN DIODE RAT	INGS AND C	CHARACTER	RISTICS				
Maximum Body-Diode Continuous Current		Is	T _C =25°C			-80	Α
Maximum Body-Diode Pulsed Current		I _{SM}	T _C =25°C			-320	Α
Drain-Source Diode Forward Voltage		V_{SD}	I _F =-80A, V _{GS} =0V		-1.2	-1.6	V

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